

Silicon PNP Power Transistors

2SA755

DESCRIPTION

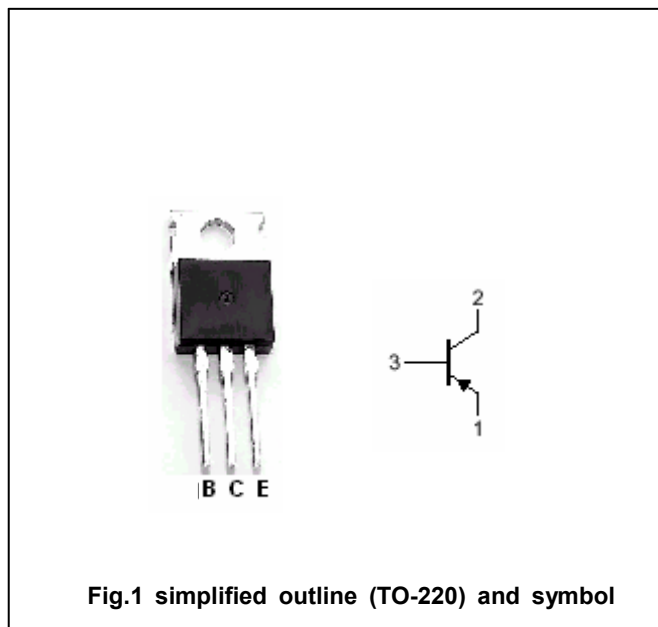
- With TO-220 package
- Complement to type 2SC1419
- Note:Type 2SA754 with short pin

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-50	V
V_{CEO}	Collector-emitter voltage	Open base	-50	V
V_{EBO}	Emitter-base voltage	Open collector	-4	V
I_C	Collector current		-2	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	20	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -50mA, R_{BE} = \infty$	-50			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -5mA, I_E = 0$	-50			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -5mA, I_C = 0$	-4			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -1.5A; I_B = -0.15A$			-1.3	V
V_{BE}	Base-emitter on voltage	$I_C = -1A; V_{CE} = -4V$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB} = -20V; I_E = 0$			-100	μA
h_{FE-1}	DC current gain	$I_C = -1A; V_{CE} = -4V$	35		200	
h_{FE-2}	DC current gain	$I_C = -0.1A; V_{CE} = -4V$	35			
f_T	Transition frequency	$I_C = -0.5A; V_{CE} = -4V$		50		MHz

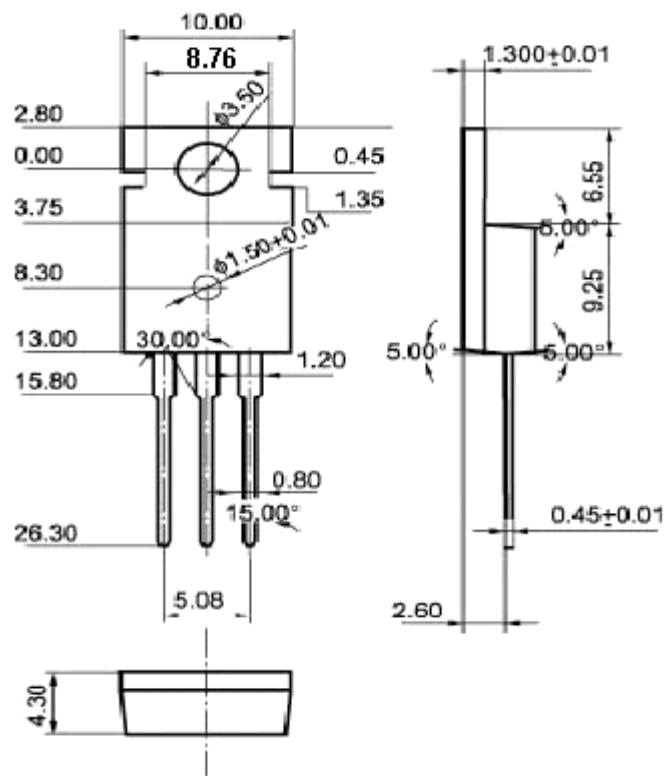
◆ h_{FE-1} Classifications

A	B	C
35-70	60-120	100-200

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PACKAGE OUTLINE

Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)